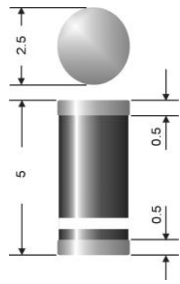


# SAM 4001 ... SAM 4007



## Surface mount diode

## Standard Avalanche Diodes

### SAM 4001 ... SAM 4007

Forward Current: 1 A

Reverse Voltage: 50 to 1000 V

### Features

- Max. solder temperature: 260 °C
- Plastic material has UL classification 94V-0

### Mechanical Data

- Plastic case: Melf / DO-213AB
- Weight approx.: 0,12 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 5000 pieces per reel

1) Max. temperature of the terminals  $T_T = 75$  °C

2)  $I_F = 1$  A,  $T_J = 25$  °C

3)  $T_A = 25$  °C

4) Mounted on P.C. board with 25 mm<sup>2</sup> copper pads at each terminal

| Type     | Polarity color band | Repetitive peak reverse voltage<br>$V_{RRM}$<br>V | Surge peak reverse voltage<br>$V_{RSM}$<br>V | Maximum forward voltage<br>$T_J = 25$ °C<br>$I_F = 1$ A<br>$V_F^{(2)}$<br>V | Maximum reverse recovery time<br>$I_F = -A$<br>$I_R = -A$<br>$I_{RR} = -A$<br>$t_{rr}$<br>ns |
|----------|---------------------|---|--|---|--|
| SAM 4001 | -                   | 50  | 50   | 1,1   | -  |
| SAM 4002 | -                   | 100   | 100  | 1,1   | -  |
| SAM 4003 | -                   | 200   | 200  | 1,1   | -  |
| SAM 4004 | -                   | 400   | 400  | 1,1   | -  |
| SAM 4005 | -                   | 600   | 600  | 1,1   | -  |
| SAM 4006 | -                   | 800   | 800  | 1,1   | -  |
| SAM 4007 | -                   | 1000  | 1000   | 1,1   | -  |

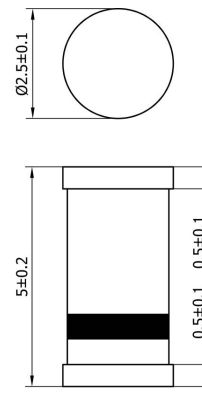
### Absolute Maximum Ratings $T_A = 25$ °C, unless otherwise specified

| Symbol    | Conditions  | Values         | Units            |
|-----------|---|----------------|------------------|
| $I_{FAV}$ | Max. averaged fwd. current, R-load, $T_T = 75$ °C <sup>1)</sup> | 1              | A                |
| $I_{FRM}$ | Repetitive peak forward current $f > 15$ Hz <sup>1)</sup>       | 10             | A                |
| $I_{FSM}$ | Peak fwd. surge current 50 Hz half sinus-wave <sup>3)</sup>     | 40             | A                |
| $I^2t$    | Rating for fusing, $t < 10$ ms <sup>3)</sup>                    | 8              | A <sup>2</sup> s |
| $R_{thA}$ | Max. thermal resistance junction to ambient <sup>4)</sup>       | 45             | K/W              |
| $R_{thT}$ | Max. thermal resistance junction to terminals                   | 10             | K/W              |
| $T_J$     | Operating junction temperature                                  | - 50 ... + 175 | °C               |
| $T_s$     | Storage temperature   | - 50 ... + 175 | °C               |

### Characteristics $T_A = 25$ °C, unless otherwise specified

| Symbol    | Conditions   | Values | Units |
|-----------|--|--------|-------|
| $I_R$     | Maximum leakage current, $T_J = 25$ °C; $V_R = V_{RRM}$<br>$T_J =$ °C; $V_R = V_{RRM}$                     | <1,5   | µA    |
| $C_J$     | Typical junction capacitance<br>(at MHz and applied reverse voltage of V)                                  | -      | pF    |
| $Q_{rr}$  | Reverse recovery charge<br>( $U_R = V$ ; $I_F = A$ ; $dI_F/dt = A/ms$ )                                    | -      | µC    |
| $E_{RSM}$ | Non repetitive peak reverse avalanche energy<br>( $L = 40$ mH; $T_J = 25$ °C; inductive load switched off) | 20     | mJ    |

Dimensions in mm



case: Melf / DO-213AB

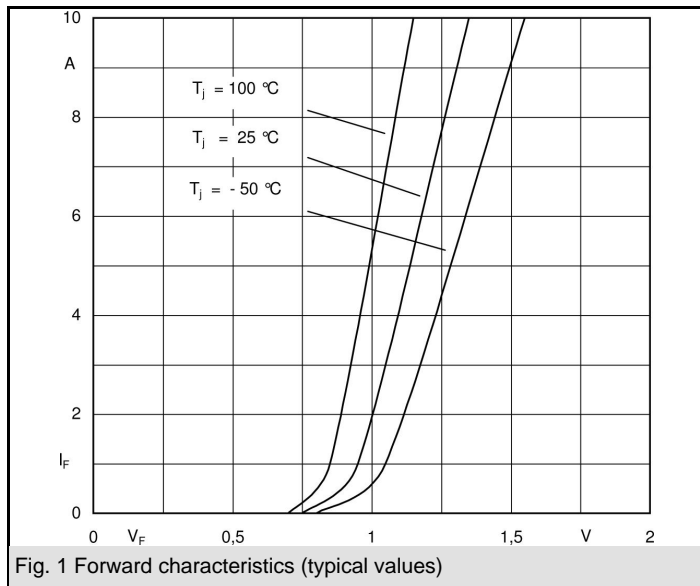


Fig. 1 Forward characteristics (typical values)

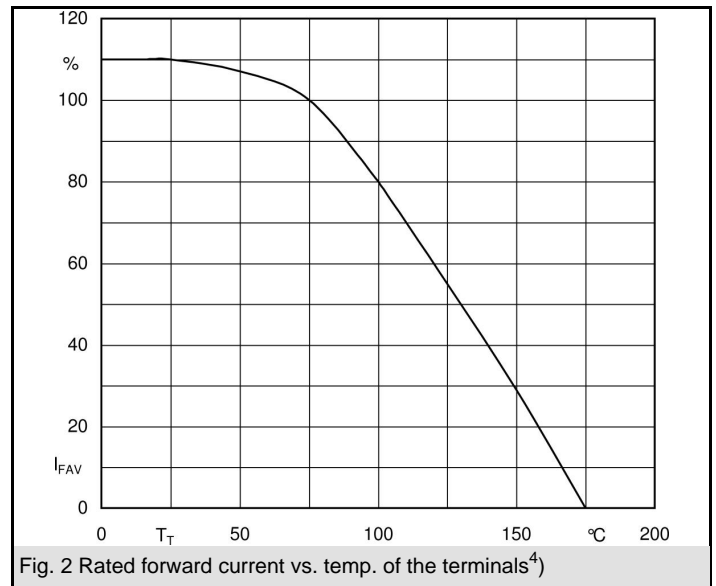


Fig. 2 Rated forward current vs. temp. of the terminals<sup>4)</sup>